



STW43NM60ND

N-channel 600 V - 0.075 Ω - 35 A - TO-247
FDmesh™ Power MOSFET (with fast diode)

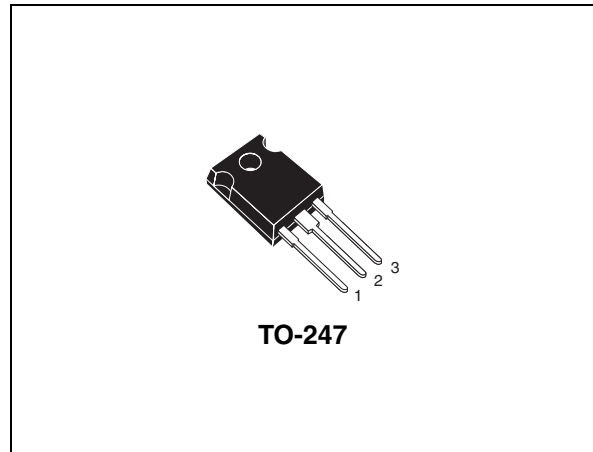
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Preliminary Data

Features

Type	V _{DSS} @ T _{JMAX}	R _{DS(on)} max	I _D
STW43NM60ND	650 V	< 0.095 Ω	35 A

- The worldwide best R_{DS(on)}*area amongst the fast recovery diode devices
- 100% avalanche tested
- Low input capacitance and gate charge
- Low gate input resistance
- Extremely high dv/dt and avalanche capabilities.



Application

- Switching applications

Description

The FDmesh™ II series belongs to the second generation of MDmesh™ technology. This revolutionary Power MOSFET associates a new vertical structure to the company's strip layout and associates all advantages of reduced on-resistance and fast switching with an intrinsic fast-recovery body diode. It is therefore strongly recommended for bridge topologies, in particular ZVS phase-shift converters.

Figure 1. Internal schematic diagram

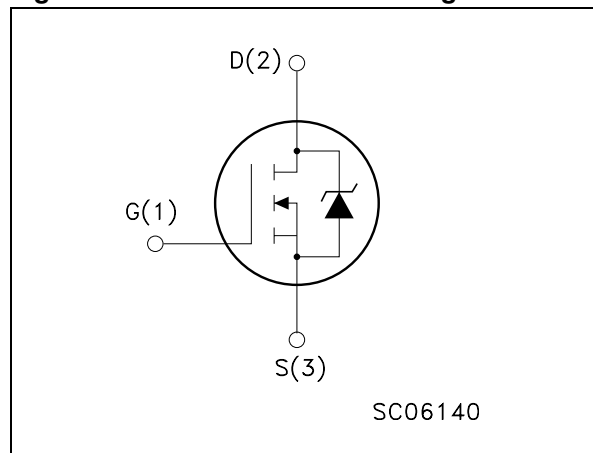


Table 1. Device summary

Order code	Marking	Package	Packaging
STW43NM60NDD	43NM60ND	TO-247	Tube

1 Electrical ratings

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Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage ($V_{GS} = 0$)	600	V
V_{GS}	Gate- source voltage	± 25	V
I_D	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	35	A
I_D	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	22.05	A
$I_{DM}^{(1)}$	Drain current (pulsed)	140	A
P_{TOT}	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	255	W
$dv/dt^{(2)}$	Peak diode recovery voltage slope	40	V/ns
T_{stg}	Storage temperature	-55 to 150	$^\circ\text{C}$
T_j	Max. operating junction temperature	150	$^\circ\text{C}$

1. Pulse width limited by safe operating area

2. $I_{SD} \leq 35\text{ A}$, $di/dt \leq 600\text{ A}/\mu\text{s}$, $V_{DD} = 80\% V_{(BR)DSS}$

Table 3. Thermal data

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case max	0.49	$^\circ\text{C}/\text{W}$
$R_{thj-amb}$	Thermal resistance junction-ambient max	50	$^\circ\text{C}/\text{W}$
T_l	Maximum lead temperature for soldering purpose	300	$^\circ\text{C}$

Table 4. Avalanche characteristics

Symbol	Parameter	Value	Unit
I_{AS}	Avalanche current, repetitive or not-repetitive (pulse width limited by T_j Max)	Tbd	A
E_{AS}	Single pulse avalanche energy (starting $T_j=25\text{ }^\circ\text{C}$, $I_D=I_{AS}$, $V_{DD}=50\text{ V}$)	Tbd	mJ

2 Electrical characteristics

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(T_{CASE} = 25 °C unless otherwise specified)**Table 5. On/off states**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V _{(BR)DSS}	Drain-source breakdown voltage	I _D = 1 mA, V _{GS} = 0	600			V
I _{DSS}	Zero gate voltage drain current (V _{GS} = 0)	V _{DS} = Max rating V _{DS} = Max rating, @125 °C			1 100	μA μA
I _{GSS}	Gate-body leakage current (V _{DS} = 0)	V _{GS} = ± 20 V			100	nA
V _{GS(th)}	Gate threshold voltage	V _{DS} = V _{GS} , I _D = 250 μA	3	4	5	V
R _{DS(on)}	Static drain-source on resistance	V _{GS} = 10 V, I _D = 17.5 A		0.075	0.095	Ω

Table 6. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
g _{fs} ⁽¹⁾	Forward transconductance	V _{DS} =15 V, I _D = 17.5 A		Tbd		S
C _{iss} C _{oss} C _{rss}	Input capacitance Output capacitance Reverse transfer capacitance	V _{DS} = 50 V, f = 1 MHz, V _{GS} = 0		4102 223 20		pF pF pF
C _{oss eq.} ⁽²⁾	Equivalent output capacitance	V _{GS} = 0, V _{DS} = 0 to 480 V		Tbd		pF
Q _g Q _{gs} Q _{gd}	Total gate charge Gate-source charge Gate-drain charge	V _{DD} = 480 V, I _D = 35 A, V _{GS} = 10 V, (see Figure 3)		137 Tbd Tbd		nC nC nC
R _g	Gate input resistance	f=1 MHz Gate DC Bias=0 Test signal level = 20 mV open drain		1.4		Ω

1. Pulsed: Pulse duration = 300 μs, duty cycle 1.5 %

2. C_{oss eq.} is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DS}**Table 7. Switching times**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
t _{d(on)} t _r t _{d(off)} t _f	Turn-on delay time Rise time Turn-off delay time Fall time	V _{DD} = 300 V, I _D = 35 A R _G = 4.7 Ω V _{GS} = 10 V (see Figure 2)		Tbd Tbd Tbd Tbd		ns ns ns ns

Table 8. Source drain diode

Symbol	Parameter	Test conditions	Min	Typ.	Max	Unit
I_{SD}	Source-drain current				35	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)				140	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 35 \text{ A}, V_{GS} = 0$			1.3	V
t_{rr}	Reverse recovery time	$I_{SD} = 35 \text{ A}, di/dt = 100 \text{ A}/\mu\text{s}$		Tbd		ns
Q_{rr}	Reverse recovery charge	$V_{DD} = 100 \text{ V}$		Tbd		μC
I_{RRM}	Reverse recovery current	(see Figure 4)		Tbd		A
t_{rr}	Reverse recovery time	$I_{SD} = 35 \text{ A}, di/dt = 100 \text{ A}/\mu\text{s}$		Tbd		ns
Q_{rr}	Reverse recovery charge	$V_{DD} = 100 \text{ V}, T_j = 150 \text{ }^\circ\text{C}$		Tbd		μC
I_{RRM}	Reverse recovery current	(see Figure 4)		Tbd		A

1. Pulse width limited by safe operating area
2. Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %

3 Test circuit

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Figure 2. Switching times test circuit for resistive load

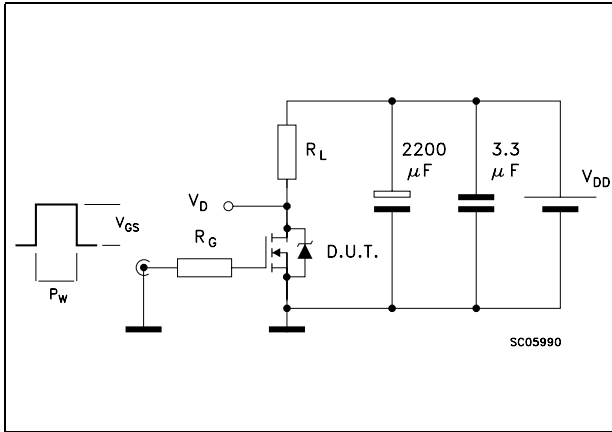


Figure 3. Gate charge test circuit

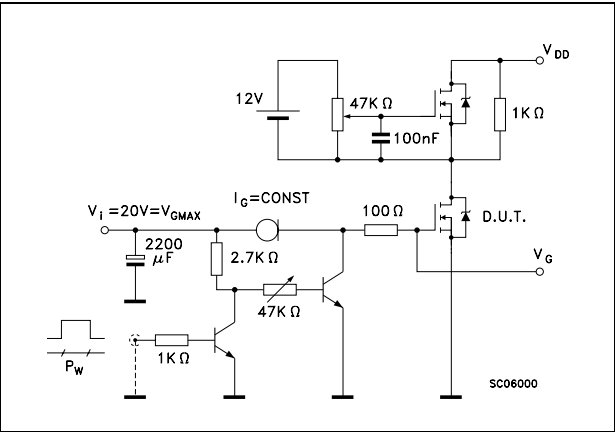


Figure 4. Test circuit for inductive load switching and diode recovery times

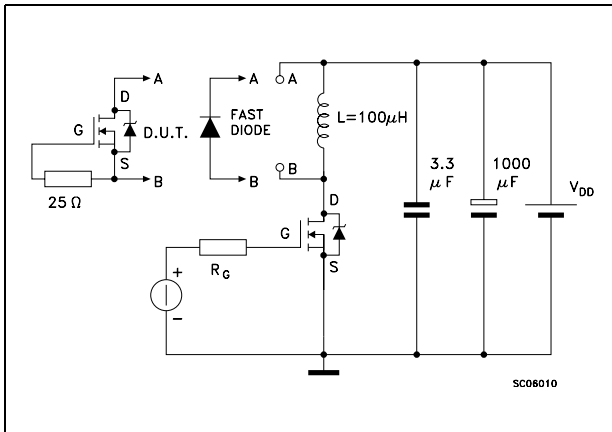


Figure 5. Unclamped Inductive load test circuit

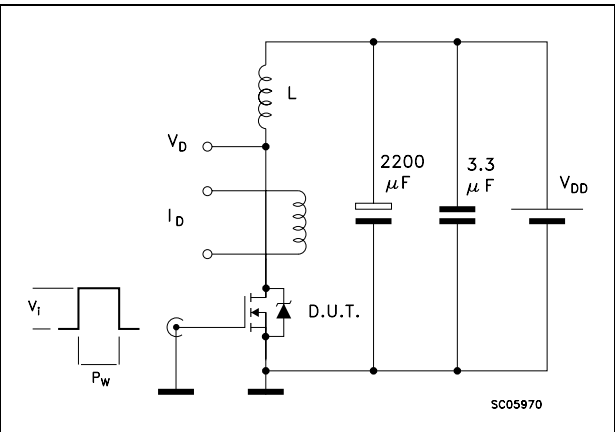


Figure 6. Unclamped inductive waveform

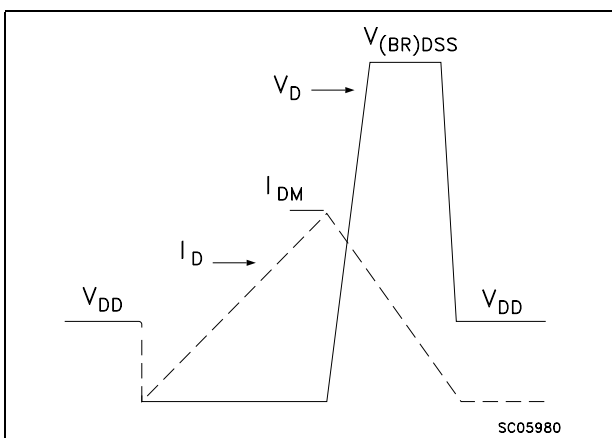
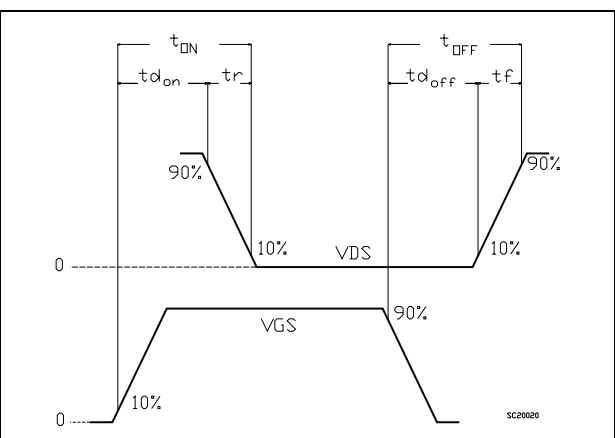


Figure 7. Switching time waveform



4 Package mechanical data

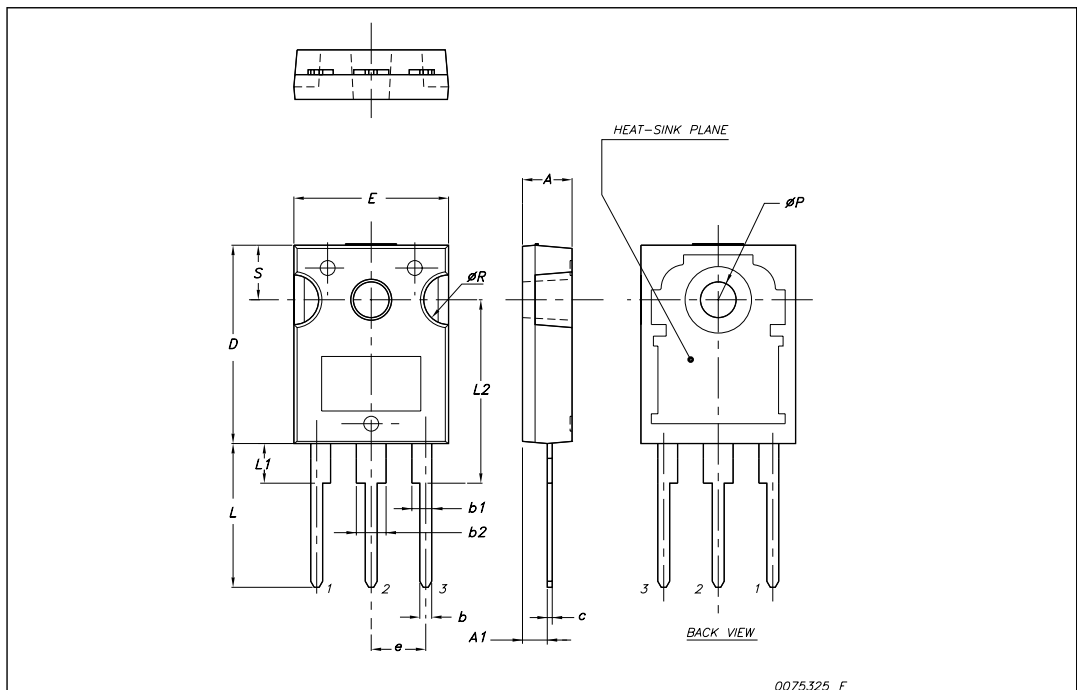
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In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

TO-247 Mechanical data

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Dim.	mm.		
	Min.	Typ	Max.
A	4.85		5.15
A1	2.20		2.60
b	1.0		1.40
b1	2.0		2.40
b2	3.0		3.40
c	0.40		0.80
D	19.85		20.15
E	15.45		15.75
e		5.45	
L	14.20		14.80
L1	3.70		4.30
L2		18.50	
øP	3.55		3.65
øR	4.50		5.50
S		5.50	



5 Revision history

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Table 9. Document revision history

Date	Revision	Changes
06-Feb-2008	1	First release

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